DHG100X600NA

Sonic Fast Recovery Diode

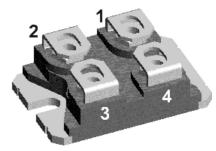
	'		
V_{RRM}	=	600 V	
I _{FAV}	<i>=</i> 2x	50 A	
t _{rr}	=	35 ns	

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High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

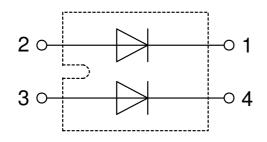
Part number

DHG100X600NA



Backside: Isolated **W**E72873

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Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Package: SOT-227B (minibloc)
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application and assentiated which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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Fast Dio	st Diode			Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	$V_{R} = 600 V$	$T_{VJ} = 25^{\circ}C$			200	μA
		$V_{R} = 600 V$	$T_{vJ} = 125^{\circ}C$			4	mA
V _F	forward voltage drop	I _F = 50 A	$T_{VJ} = 25^{\circ}C$			2.20	V
		I _F = 100 A				2.95	V
		$I_{F} = 50 \text{ A}$	T _{vJ} = 125°C			2.18	V
		$I_{F} = 100 \text{ A}$				3.10	V
IFAV	average forward current	$T_c = 60^{\circ}C$	T _{vJ} = 150°C			50	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{vJ} = 150$ °C			1.20	V
r _F	slope resistance } for power in	oss calculation only				19	mΩ
R _{thJC}	thermal resistance junction to cas	e				0.6	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.10		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			210	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_{R} = 0 V$	$T_{vJ} = 45^{\circ}C$			430	Α
C	junction capacitance	V_{R} = 400 V f = 1 MHz	$T_{v_J} = 25^{\circ}C$		47		pF
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 ^{\circ}C$		20		Α
		$I_{\rm F} = 50 \text{A}; V_{\rm R} = 400 \text{V}$	T _{vJ} = 125 °C		tbd		Α
t _{rr}	reverse recovery time	$\begin{cases} I_{F} = 50 \text{ A}; V_{R} = 400 \text{ V} \\ -di_{F} / dt = 1200 \text{ A} / \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		35		ns
)	T _{vJ} = 125 °C		tbd		ns

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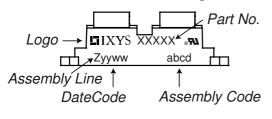
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Package	Package SOT-227B (minibloc)			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					150	А
T _{vj}	virtual junction temperature)			-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
M _T	terminal torque				1.1		1.5	Nm
d _{Spp/App}	araanaa diatanaa an ayyfa	and latriking distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage distance on suna	ace striking distance through air	terminal to backside	8.6	6.8			mm
	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		2500			V

Product Marking



Part description

D = Diode H = Sonic Fast Recovery Diode

G = extreme fast

100 = Current Rating [A]

X = Parallel legs 600 = Reverse Voltage [V]

NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG100X600NA	DHG100X600NA	Tube	10	510840

Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 150 °C
)R_o	Fast Diode		
V _{0 max}	threshold voltage	1.2		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	17		mΩ

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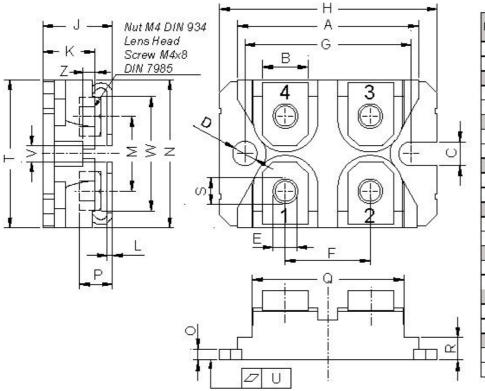
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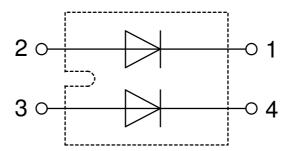
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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
Dirn.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
К	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Ρ	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	
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